

KBP SILICON BRIDGE RECTIFIERV

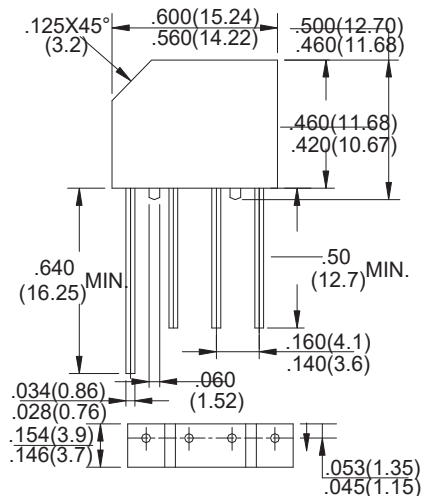
FEATURES

- The plastic package carries Underwrites Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- High reliability
- High temperature soldering guaranteed:260 °C/10 seconds at terminals
- Component in accordance to RoHs 2015/863 and WEEE

2012/19/EU

MECHANICAL DATA

- Case style: KBP molded plastic
- Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

TYPE NUMBER	SYMBOL	KBP 2005	KBP 201	KBP 202	KBP 204	KBP 206	KBP 208	KBP 210	UNITS
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
	V _{RWM}								
	V _{DC}								
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average Rectified Output Current @T _A =50 °C	I _O	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	60							A
Forward Voltage per element @I _F =2.0A	V _{FM}	1.1							V
Peak Reverse Current @T _A =25°C At Rated DC Blocking Voltage @T _A =125°C	I _R	5.0 500							uA
Typical Thermal Resistance per leg	R _{θJA}	25							°C/W
	R _{θJL}	8							
Operating and Storage Temperature Range	T _J , T _{STG}	-55to+150							°C

RATINGS AND CHARACTERISTIC CURVES

Fig. 1 Forward Current Derating Curve

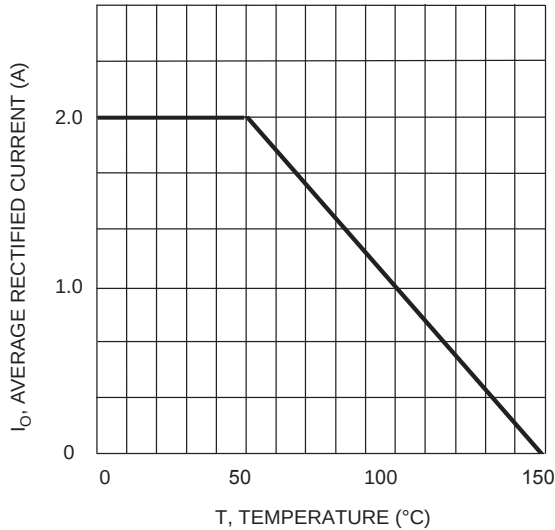


Fig. 2 Typical Fwd Characteristics

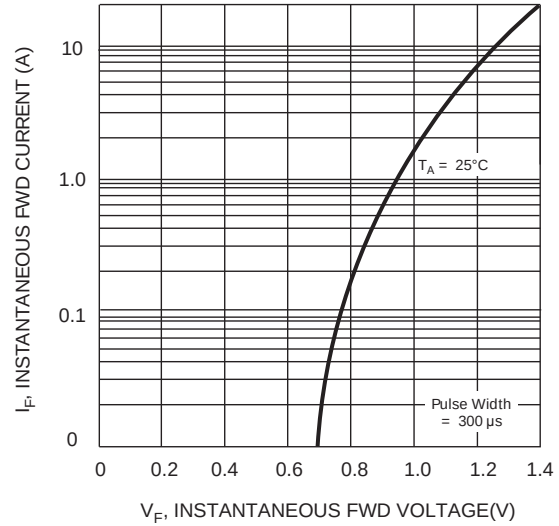


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

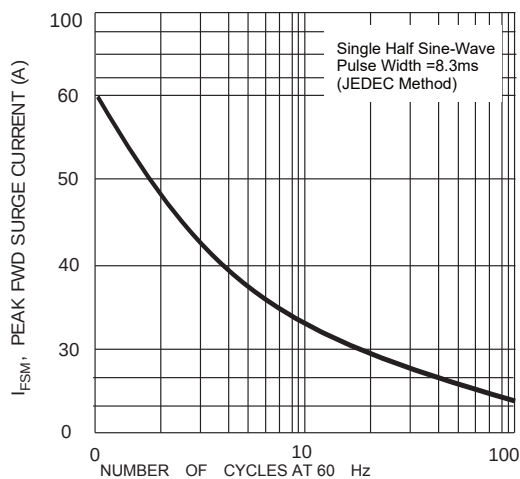


Fig. 4 Typical Junction Capacitance

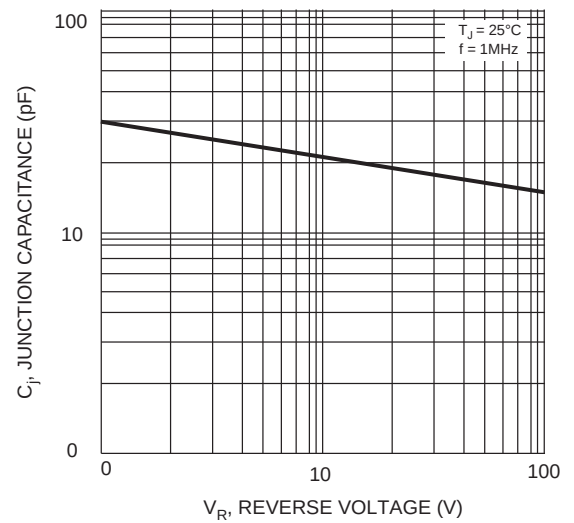


Fig.5-typical Reverse Characteristics (per element)

